Photocouplers Infrared LED & Photo IC

TLP2160

1. Applications

- Factory Networking
- High-Speed Digital Interfacing for Instrumentation and Control Devices
- Plasma Display Panels (PDPs)

2. General

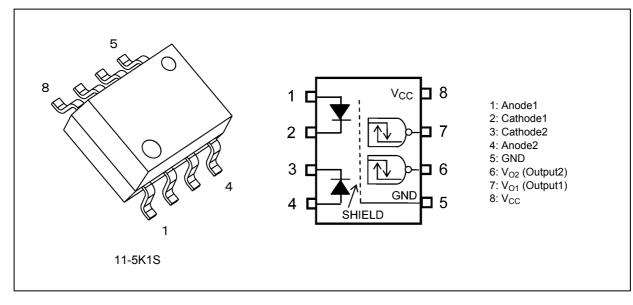
The Toshiba TLP2160 consists of a high-output infrared LED coupled with a high-speed photo IC chip. TLP2160 guarantees operation at up to 125°C and on supplies from 2.7 V to 5.5 V. It is offered in the SO8 package. It has a totem-pole output that can both sink and source current. With two LED-photoreceptor pairs, the TLP2160 helps save board space. An internal noise shield provides a guaranteed common-mode transient immunity of 20 kV/ μ s.

3. Features

- (1) Inverter logic type (totem pole output)
- (2) Package: SO8
- (3) Operating temperature range: -40 to 125 $^{\circ}\text{C}$
- (4) Supply voltage: 2.7 to 5.5 V
- (5) Data transfer rate: 20 MBd (typ.) (NRZ)
- (6) Threshold input current: 3.5 mA (max)
- (7) Supply current: 5 mA (max)
- (8) Common-mode transient immunity: $\pm 20 \text{ kV/}\mu \text{s}$ (min)
- (9) Isolation voltage: 2500 Vrms (min)
- (10) Safety standards
 - UL-recognized: UL 1577, File No.E67349
 - cUL-recognized: CSA Component Acceptance Service No.5A File No.E67349
 - VDE-approved: EN 60747-5-5 (Note 1)

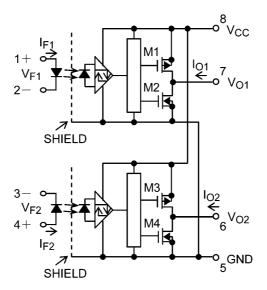
Note 1: When a VDE approved type is needed, please designate the Option (V4).

4. Packaging and Pin Assignment



Start of commercial production 2011-03 2019-11-21 Rev.4.0

5. Internal Circuit (Note)



Note: A $0.1-\mu F$ bypass capacitor must be connected between pin 8 and pin 5.

6. Principle of Operation

6.1. Truth Table

Input	LED1(2)	M1(3)	M2(4)	Output1(2)
Н	ON	OFF	ON	L
L	OFF	ON	OFF	Н

6.2. Mechanical Parameters

Characteristics	Min	Unit
Creepage distances	4.2	mm
Clearance distances	4.2	
Internal isolation thickness	—	

7. Absolute Maximum Ratings (Note) (Unless otherwise specified, T_a = 25 °C)

	Characteristics		Symbol	Note	Rating	Unit
LED	Input forward current		١ _F	(Note 1)	25	mA
	Input forward current derating	(T _a ≥ 110 °C)	$\Delta I_F / \Delta T_a$	(Note 1)	-0.67	mA/°C
	Input forward current (pulsed)		I _{FP}	(Note 1), (Note 2)	40	mA
	Input forward current derating (pulsed)	(T _a ≥ 110 °C)	$\Delta I_{FP} / \Delta T_a$	(Note 1)	-1.0	mA/°C
	Input power dissipation		PD	(Note 1)	40	mW
	Input power dissipation derating	$(T_a \ge 110 \ ^\circ C)$	$\Delta P_D / \Delta T_a$	(Note 1)	-1.0	mW/°C
	Input reverse voltage		V _R	(Note 1)	5	V
Detector	Output current		I _O	(Note 1)	10	mA
	Output voltage		Vo	(Note 1)	6	V
	Supply voltage		V _{CC}		6	
	Output power dissipation		Po	(Note 1)	60	mW
	Output power dissipation derating	$(T_a \ge 110 \ ^\circ C)$	$\Delta P_0 / \Delta T_a$	(Note 1)	-1.5	mW/°C
Common	Operating temperature		T _{opr}		-40 to 125	°C
	Storage temperature		T _{stg}		-55 to 150	
	Lead soldering temperature	(10 s)	T _{sol}		260	
	Isolation voltage	(AC, 60 s, R.H. ≤ 60 %)	BVS	(Note 3)	2500	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Each channel

- Note 2: Pulse width (PW) \leq 1 ms, duty = 50 %
- Note 3: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

8. Recommended Operating Conditions (Note)

Characteristics	Symbol	Note	Min	Тур.	Max	Unit
Input on-state current	I _{F(ON)}	(Note 1), (Note 2)	4.5	—	15	mA
Input off-state voltage	V _{F(OFF)}	(Note 1)	0		0.8	V
Supply voltage	V _{CC}	(Note 3)	2.7	3.3 / 5	5.5	
Operating temperature	T _{opr}	(Note 3)	-40		125	°C

Note: The recommended operating conditions are given as a design guide necessary to obtain the intended performance of the device. Each parameter is an independent value. When creating a system design using this device, the electrical characteristics specified in this data sheet should also be considered.

Note: A ceramic capacitor (0.1 μF) should be connected between pin 8 and pin 5 to stabilize the operation of a highgain linear amplifier. Otherwise, this photocoupler may not switch properly. The bypass capacitor should be placed within 1 cm of each pin.

Note 1: Each channel

Note 2: The rise and fall times of the input on-current should be less than 0.5 $\mu s.$

Note 3: Denotes the operating range, not the recommended operating condition.

Electrical Characteristics (Note) (Unless otherwise specified, T_a = -40 to 125 °C, V_{CC} = 2.7 to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Lest Condition		Тур.	Max	Unit
Input forward voltage	V _F	(Note 1)		I _F = 10 mA, T _a = 25 °C	1.45	1.55	1.7	V
Input forward voltage temperature coefficient	$\Delta V_{F} / \Delta T_{a}$	(Note 1)		I _F = 10 mA	_	-2.0		mV/°C
Input reverse current	I _R	(Note 1)		V _R = 5 V, T _a = 25 °C	_	_	10	μA
Input capacitance	Ct	(Note 1)		V = 0 V, f = 1 MHz , T _a = 25 °C	_	60	_	pF
Low-level output voltage	V _{OL}	(Note 1)	Fig. 12.1.1	I _F = 14 mA, I _O = 4 mA	_		0.4	V
High-level output voltage	V _{OH}	(Note 1)	Fig. 12.1.2	V _F = 1.05 V, I _O = -4 mA, V _{CC} = 3.3 V	2.3		_	
				V _F = 1.05 V, I _O = -4 mA, V _{CC} = 5 V	4		_	
Low-level supply current	I _{CCL}		Fig. 12.1.3	I _{F1} = I _{F2} = 14 mA	—	_	5	mA
High-level supply current	I _{CCH}		Fig. 12.1.4	$I_{F1} = I_{F2} = 0 \text{ mA}$	—	_	5	
Threshold input current (H/L)	I _{FHL}	(Note 1)		I _O = 1.6 mA, V _O < 0.4 V	_	_	3.5	

Note: All typical values are at V_{CC} = 5.0 V, T_a = 25 °C.

Note 1: Each channel

10. Isolation Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Note Test Condition		Min	Тур.	Max	Unit
Total capacitance (input to output)	Cs	(Note 1)	V = 0 V, f = 1 MHz	—	0.8	—	рF
Isolation resistance	R _S	(Note 1)	V = 500 V, R.H. ≤ 60 %	10 ¹²	10 ¹⁴		Ω
Isolation voltage	BVS	(Note 1)	AC, 60 s	2500			Vrms

Note 1: This device is considered as a two-terminal device: Pins 1, 2, 3 and 4 are shorted together, and pins 5, 6, 7 and 8 are shorted together.

11. Switching Characteristics (Note)

11.1. Switching Characteristics (1) (Unless otherwise specified, $T_a = -40$ to 125 °C, $V_{CC} = 2.7$ to 3.6 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	$\begin{array}{l} I_F = 0 \rightarrow 14 \text{ mA}, R_{\text{IN}} = 100 \; \Omega, \\ C_L = 15 \; \text{pF} \end{array}$	—	30	40	ns
Propagation delay time (L/H)	t _{pLH}	(Note 1)		$ I_F = 14 \rightarrow 0 \text{ mA}, \text{R}_{\text{IN}} = 100 \Omega, \text{C}_{\text{L}} $ = 15 pF	—	25	40	
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		I_F = 14 mA, R _L = 100 Ω, C _L = 15 pF	—	5	25	ns
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)		I_F = 14 mA, R _{IN} = 100 Ω, C _L = 15 pF	-30		30	ns
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	$\begin{array}{l} I_{F} = 0 \rightarrow 6 \text{ mA } R_{IN} = 100 \; \Omega, \\ C_{L} = 15 \; pF \end{array}$	—	36	55	
Propagation delay time (L/H)	t _{pLH}	(Note 1)		$ I_F = 6 \rightarrow 0 \text{ mA}, R_{\text{IN}} = 100 \Omega, \\ C_L = 15 \text{ pF} $	—	26	55	ns
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		I_F = 6 mA, R _{IN} = 100 Ω, C _L = 15 pF	—	10	30	ns
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)		I _F = 6 mA, R _{IN} = 100 Ω, C _L = 15 pF	-30		30	ns
Fall time	t _f	(Note 1)	Fig. 12.1.5	$\begin{array}{l} I_{F} = 0 \rightarrow 14 \text{ mA}, R_{IN} = 100 \; \Omega, \\ C_{L} = 15 \; \text{pF} \end{array}$	—	15	_	ns
Rise time	t _r	(Note 1)		$\begin{array}{l} I_{F} = 14 \rightarrow 0 \text{ mA}, R_{IN} = 100 \; \Omega, \\ C_{L} = 15 \; \text{pF} \end{array}$	—	15	_	ns
High-level common-mode transient immunity	CM _H		Fig. 12.1.6	$V_{CM} = 1000 V_{p-p}, I_F = 0 mA, V_O(min) = 2 V, V_{CC} = 3.3 V, T_a = 25 °C$	±20	±25	—	kV/μs
Low-level common-mode transient immunity	CML			V_{CM} = 1000 V _{p-p} , I _F = 14 mA, V _O (max) = 0.4 V,V _{CC} = 3.3 V, T _a = 25 °C	±20	±25	—	kV/μs

Note: All typical values are at V_{CC} = 3.3 V, T_a = 25 °C.

Note: Each channel

Note 1: f = 5 MHz, duty = 50 %, input current $t_r = t_f$ = less than 5 ns, C_L is less than 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc.).

11.2. Switching Characteristics (2) (Unless otherwise specified, T_a = -40 to 125 °C, V_{CC} = 4.5 to 5.5 V)

Characteristics	Symbol	Note	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Propagation delay time (H/L)	t _{pHL}	(Note 1)		I_F = 0 \rightarrow 14 mA, R_{IN} = 100 Ω , C_L = 15 pF	—	33	45	ns
Propagation delay time (L/H)	t _{pLH}	(Note 1)		I_F = 14 \rightarrow 0 mA, R _{IN} = 100 Ω, C _L = 15 pF	—	25	45	ns
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		I_F = 14 mA, R_{IN} = 100 Ω, C_L = 15 pF	—	8	25	ns
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)		I _F = 14 mA, R _{IN} = 100 Ω, C _L = 15 pF	-30	—	30	ns
Propagation delay time (H/L)	t _{pHL}	(Note 1)	Fig. 12.1.5	$\begin{array}{l} I_{F} = 0 \rightarrow 6 \; mA, R_{IN} = 100 \; \Omega, \\ C_{L} = 15 \; pF \end{array}$	—	40	55	ns
Propagation delay time (L/H)	t _{pLH}	(Note 1)		$I_F = 6 \rightarrow 0 \text{ mA}, R_{IN} = 100 \Omega,$ $C_L = 15 \text{ pF}$	_	28	55	ns
Pulse width distortion	t _{pHL} - t _{pLH}	(Note 1)		I _F = 6 mA, R _{IN} = 100 Ω, C _L = 15 pF	_	12	30	ns
Propagation delay skew (device to device)	t _{psk}	(Note 1), (Note 2)		I _F = 6 mA, R _{IN} = 100 Ω, C _L = 15 pF	-30	—	30	ns
Fall time	t _f	(Note 1)		I_F = 0 \rightarrow 14 mA, R_{IN} = 100 Ω , C_L = 15 pF	—	15		ns
Rise time	t _r	(Note 1)		I_F = 14 \rightarrow 0 mA, R _{IN} = 100 Ω, C _L = 15 pF	—	15	_	ns
High-level common-mode transient immunity	CM _H			$V_{CM} = 1000 V_{p-p}, I_F = 0 mA,$ $V_O(min) = 4 V, V_{CC} = 5 V,$ $T_a = 25 °C$	±20	±25	_	kV/μs
Low-level common-mode transient immunity	CML			V_{CM} = 1000 V _{p-p} , I _F = 14 mA, V _O (max) = 0.4 V, V _{CC} = 5 V, T _a = 25 °C	±20	±25	—	kV/μs

Note: All typical values are at $V_{CC} = 5 V$, $T_a = 25 °C$.

Note: Each channel

Note 1: f = 5 MHz, duty = 50 %, input current $t_r = t_f$ = less than 5 ns, C_L is less than 15 pF which includes probe and stray wiring capacitance.

Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc.).

12. Test Circuits and Characteristics Curves

12.1. Test Circuits

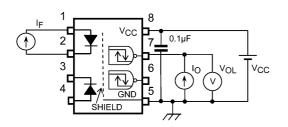
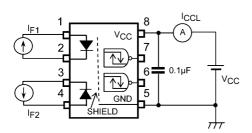


Fig. 12.1.1 V_{OL} Test Circuit





I_F = 6/14 mA (P.G.)

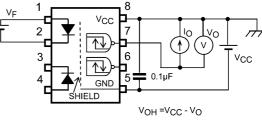


Fig. 12.1.2 V_{OH} Test Circuit

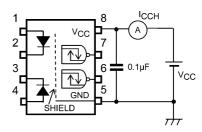
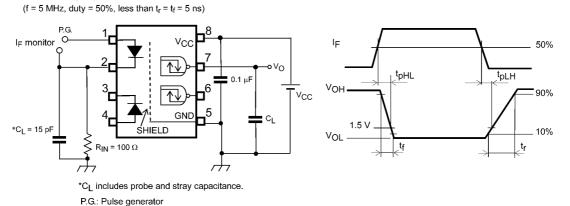


Fig. 12.1.4 I_{CCH} Test Circuit





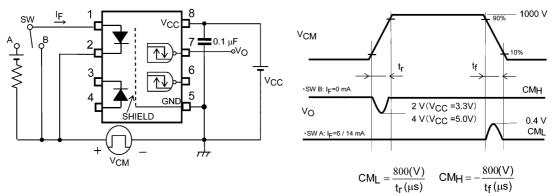
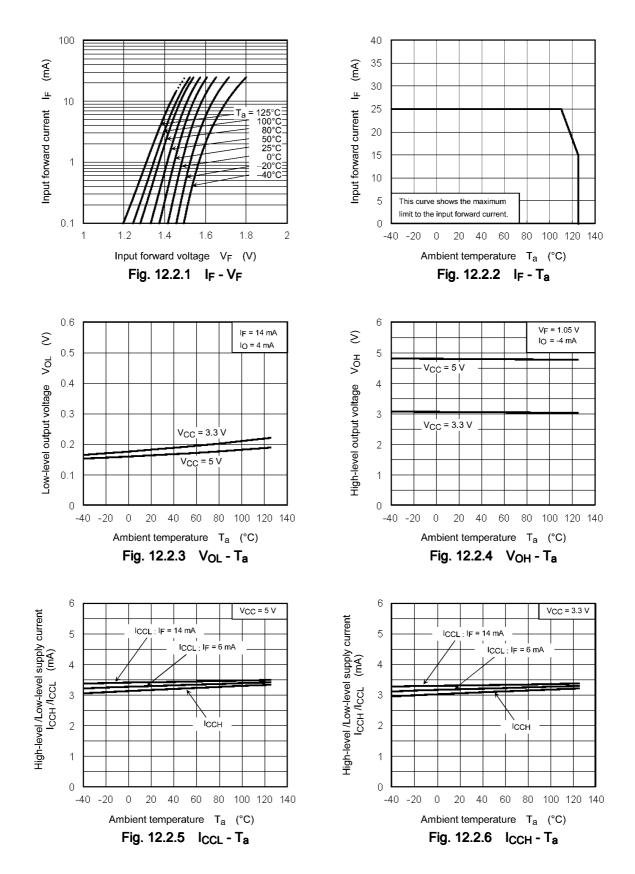
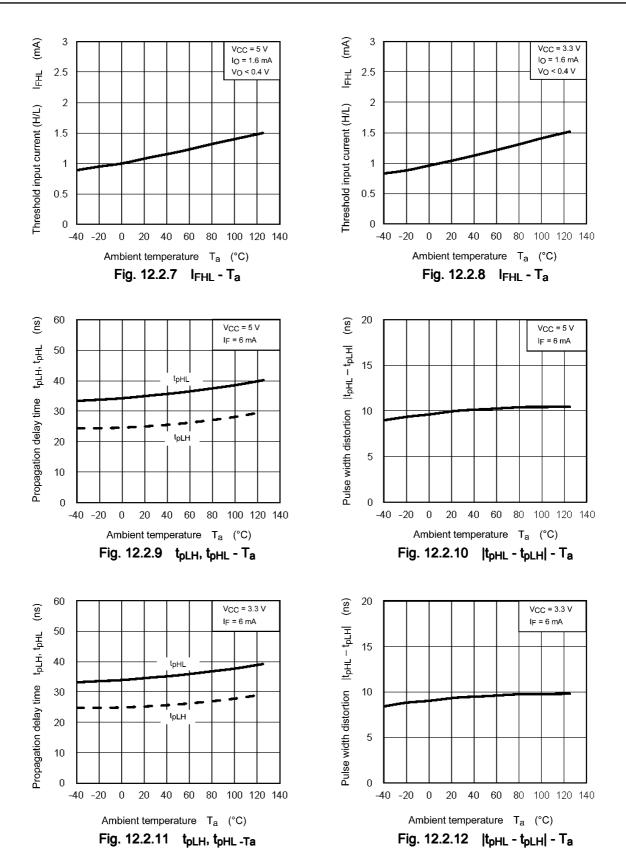
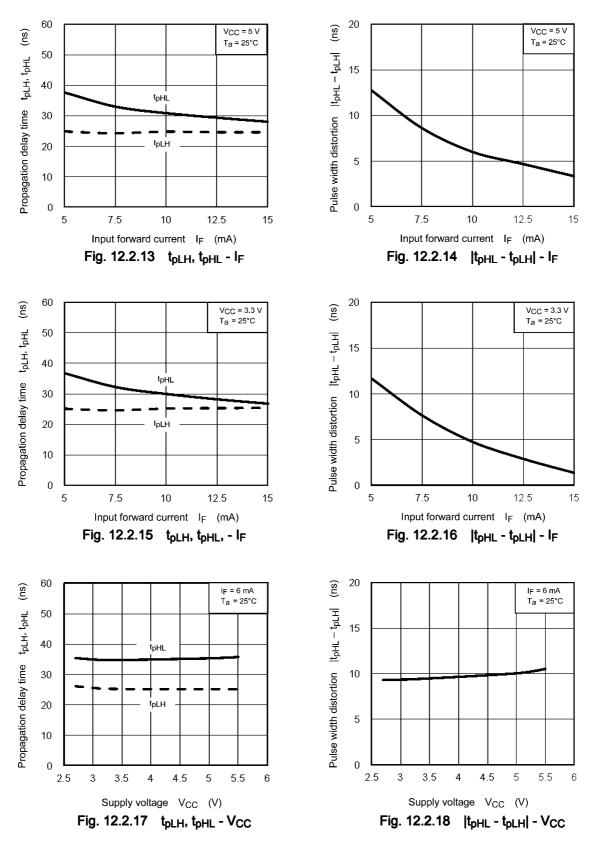


Fig. 12.1.6 Common-Mode Transient Immunity Test Circuit and Waveform

12.2. Characteristics Curves (Note)







Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

13. Soldering and Storage

13.1. Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

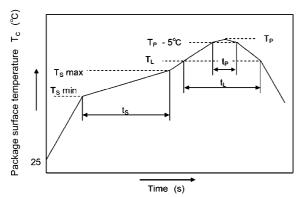
• When using soldering reflow.

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be completed with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	s
Ramp-up rate $(T_L \text{ to } T_P)$			3	°C/s
Liquidus temperature	TL	2	17	°C
Time above T_{L}	tL	60	150	s
Peak temperature	Τ _Ρ		260	°C
Time during which T_c is between (T _P – 5) and T _P	t₽		30	s
Ramp-down rate $(T_P \text{ to } T_L)$			6	°C/s

Fig. 13.1.1 An Example of a Temperature Profile When Lead(Pb)-Free Solder Is Used

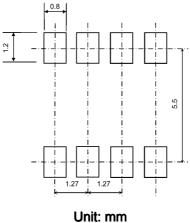
- When using soldering flow Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 120 seconds. Mounting condition of 260 °C within 10 seconds is recommended. Flow soldering must be performed once.
- When using soldering Iron (Applicable to both eutectic solder and Lead(Pb)-Free solder) Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C

Heating by soldering iron must be done only once per lead.

13.2. Precautions for General Storage

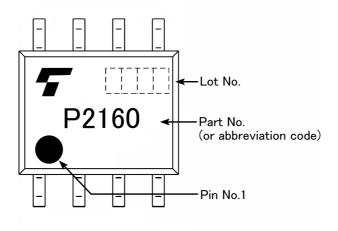
- · Avoid storage locations where devices may be exposed to moisture or direct sunlight
- Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %, respectively.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation or corrosion, which will deteriorate the solderability of the leads.
- When restoring devices after removal from their packing, use anti-static containers.
- Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

14. Land Pattern Dimensions (for reference only)



Unit. I

15. Marking



16. EN 60747-5-5 Option (V4) Specification

- Part number: TLP2160 (Note 1)
- The following part naming conventions are used for the devices that have been qualified according to option (V4) of EN 60747.

Example: TLP2160(V4-TP,F)

V4: EN 60747 option TP: Tape type F: [[G]]/RoHS COMPATIBLE **(Note 2)**

Note 1: Use TOSHIBA standard type number for safety standard application.

e.g., TLP2160(V4-TP,F) \rightarrow TLP2160

Note 2: Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Description	Symbol	Rating	Unit
Application classification			
for rated mains voltage \leq 150 Vrms for rated mains voltage \leq 300 Vrms		I-IV I-III	-
Climatic classification		40 / 125 / 21	_
Pollution degree		2	_
Maximum operating insulation voltage	VIORM	565	Vpeak
Input to output test voltage, Method A $V_{pr} = 1.6 \times V_{IORM}$, type and sample test $t_p = 10$ s, partial discharge < 5 pC	V _{pr}	904	Vpeak
Input to output test voltage, Method B V_{pr} = 1.875 × V _{IORM} , 100 % production test t_p = 1 s, partial discharge < 5 pC	V _{pr}	1059	Vpeak
Highest permissible overvoltage (transient overvoltage, t _{pr} = 60 s)	VTR	4000	Vpeak
Safety limiting values (max. permissible ratings in case of fault, also refer to thermal derating curve) current (input current I _F , P _{so} = 0) power (output or total power dissipation) temperature	I _{si} P _{so} T _s	250 400 150	mA mW °C
Insulation resistance $V_{IO} = 500 \text{ V}, \text{ T}_a = 25 \text{ °C}$ $V_{IO} = 500 \text{ V}, \text{ T}_a = 100 \text{ °C}$ $V_{IO} = 500 \text{ V}, \text{ T}_a = \text{ T}_s$	R _{si}	$\ge 10^{12}$ $\ge 10^{11}$ $\ge 10^{9}$	Ω

Fig. 16.1 E	EN 60747	Isolation	Characteristics
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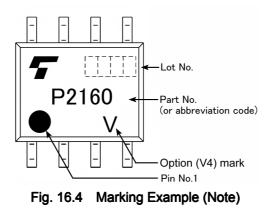
Minimum creepage distance	Cr	4.2 mm
Minimum clearance	CI	4.2 mm
Minimum insulation thickness	ti	
Comparative tracking index	СТІ	175

Fig. 16.2	Insulation Related Specification	s (Note)
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Note: This photocoupler is suitable for **safe electrical isolation** only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

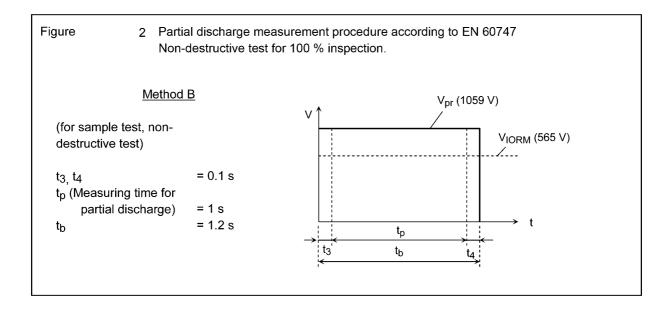


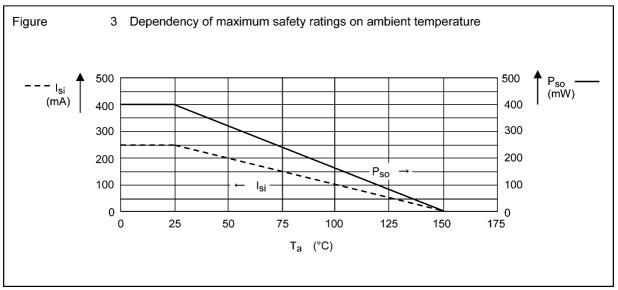


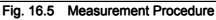


Note: The above marking is applied to the photocouplers that have been qualified according to option (V4) of EN 60747.

-gane	-	asurement procedure according to EN 60747 ualification and sampling tests.
Method	<u>A</u>	VINITIAL (4 KV)
(for type and sampling tests, destructive tests)		V V _{pr} (904 V)
t ₁ , t ₂	= 1 to 10 s	V _{IORM} (565 V)
t3, t4	= 1 s	
t _p (Measuring time for		
partial discharge)	= 10 s	$0 \xrightarrow{I} \qquad \qquad$
t _b	= 12 s	t_3 t_p t_4
t _{ini}	= 60 s	t ₁ t _{ini} t ₂ t _b







17. Ordering Information

When placing an order, please specify the part number, tape type and quantity as shown in the following example.

Example) TLP2160 (TP,F) 2500 pcs

Part number: TLP2160 Tape type: TP [[G]]/RoHS COMPATIBLE: F **(Note)** Quantity (must be a multiple of 2500)

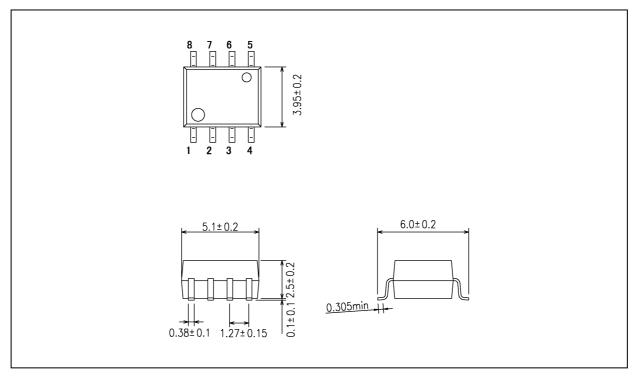
Note : Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility. RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

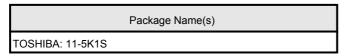
TLP2160

Package Dimensions

Unit: mm



Weight: 0.11 g (typ.)



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